

ABSTRACT OF THE DISCLOSURE

A method of forming openings in the dielectric layer. The method includes an ion implantation step to reduce a lateral etching in a chemical vapor etching step, and to provide a high etching selectivity ratio of the dielectric layer to a mask. The dry
5 etching process is partially substituted by the chemical vapor etching step, so that an opening having a straight profile is formed in the dielectric layer. Consequently, problems, such as loss of critical dimension and striation of the opening caused by loss of the mask can be effectively ameliorated.

0
1
2
3
4
5
6
7
8
9
10
11
12
13
14
15
16
17
18
19
20
21
22
23
24
25